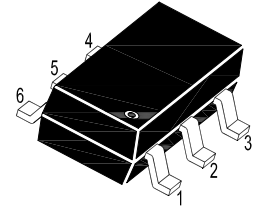
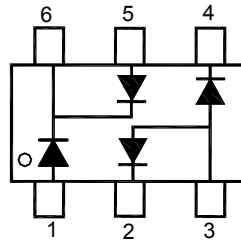


## BAV756DW

### Silicon Epitaxial Planar Switching Diode

#### Features

- High speed
- High switching speed



1. A1 2. K1 3. CA  
4. K2 5. A2 6. CC  
Marking Code: B7  
SOT-363 Plastic package

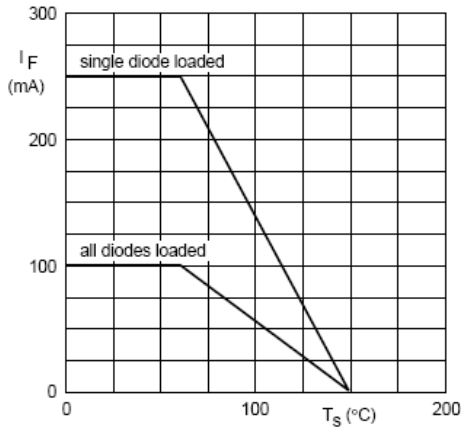
#### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	85	V
Reverse Voltage	$V_R$	75	V
Continuous Forward Current	$I_F$	250	mA
Single Diode Loaded All Diodes Loaded		100	
Repetitive Peak Forward Current	$I_{FRM}$	450	mA
Non-Repetitive Peak Forward Surge Current	$I_{FSM}$	at $t = 1 \mu\text{s}$	4
		at $t = 1 \text{ms}$	1
		at $t = 1 \text{s}$	0.5
Total Power Dissipation	$P_{tot}$	350	mW
Junction Temperature	$T_j$	- 65 to + 150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

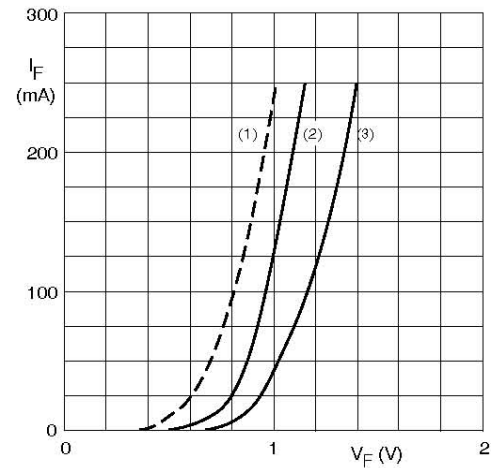
#### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1 \text{mA}$ at $I_F = 10 \text{mA}$ at $I_F = 50 \text{mA}$ at $I_F = 150 \text{mA}$	$V_F$	0.715	V
		0.855	
		1	
		1.25	
Reverse Current at $V_R = 25 \text{V}$ at $V_R = 75 \text{V}$ at $V_R = 25 \text{V}$ , $T_j = 150^\circ\text{C}$ at $V_R = 75 \text{V}$ , $T_j = 150^\circ\text{C}$	$I_R$	30	nA
		2.5	$\mu\text{A}$
		60	$\mu\text{A}$
		100	$\mu\text{A}$
Diode Capacitance at $V_R = 0$ , $f = 1 \text{MHz}$	$C_d$	2	pF
Reverse Recovery Time at $I_F = I_R = 10 \text{mA}$ , $I_{rr} = 0.1 \times I_R$ , $R_L = 100 \Omega$	$t_{rr}$	4	ns

## BAV756DW

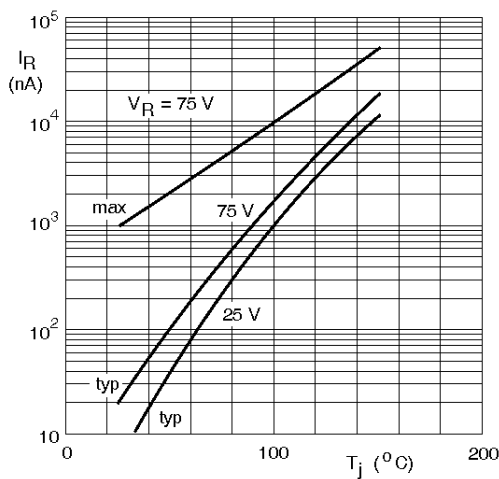


Maximum permissible continuous forward current as a function of soldering point temperature.

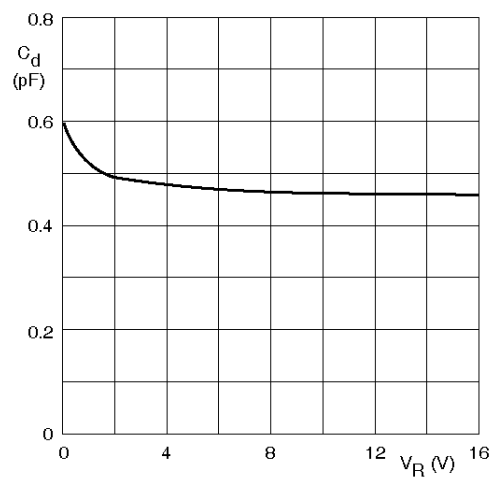


- (1)  $T_j = 150$  °C; typical values.
- (2)  $T_j = 25$  °C; typical values.
- (3)  $T_j = 25$  °C; maximum values.

Forward current as a function of forward voltage.



Reverse current as a function of junction temperature.



$f = 1$  MHz;  $T_j = 25$  °C.

Diode capacitance as a function of reverse voltage; typical values.